

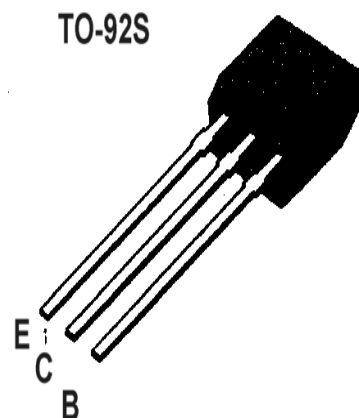
PNP Transistors

—PNP Silicon—

■■ APPLICATION: Low Frequency Amplifier Applications.

■■ MAXIMUM RATINGS (Ta=25℃)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.15	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃



■■ ELECTRICAL CHARACTERISTICS (Ta=25℃, RG=10Ω)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	$I_C=-20\mu A$	$I_E=0$	
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50			V	$I_C=-1mA$	$I_B=0$	
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E=-20\mu A$	$I_C=0$	
Collector Cut-off Current	I_{CBO}			-0.1	μA	$V_{CB}=-50V$	$I_E=0$	
Emitter Cut-off Current	I_{EBO}			-0.1	μA	$V_{EB}=-5V$	$I_C=0$	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	$I_C=-0.1A$	$I_B=-10mA$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	$I_C=-0.1A$	$I_B=-10mA$	
DC Current Gain	H_{FE}	70		400	β	$V_{CE}=-6V$	$I_C=-2mA$	
Gain bandwidth product	f_T	100	150		MHz	$V_{CE}=-6V$	$I_C=-20mA$	
Common Base Output Capacitance	C_{ob}		13		pF	$V_{CB}=-6V$	$I_E=0$	$f=1MHz$
Noise Figure	NF		1	10	dB	$V_{ce}=-6V$	$I_E=0$	$f=1MHz$

■■ hFE Classification And Marking

Print Mark	A1015		
Classification	O	Y	GR
HFE	70~140	120~240	200~400